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A READ-ONLY MEMORY PROGRAMMER/VERIFIER

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## READ-ONLY MEMORY PROGRAMMER/VERIFIER

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Technological achievement has provided us with the programmable/erasable read-only memory! A programmer for this type of memory has been built and is shown in the picture.



The ROM (Read Only Memory) operates by means of the stored charge principle and will retain data for up to ten years. Or, the ROM may be erased with intense ultra-violet light which discharges the small gate capacitance of the memory cell field effect transistors. The ROM provides an easy and compact means for code conversion. Any combination and number (up to eight for a single ROM) of binary input lines may be translated to any other combination and number (up to eight for a single ROM) of output binary lines:



Thus, the Intel ROM Type 1702 is an 8 x 8 array of memory cells which is 2048 bits in size. It is anticipated that the ROM system will find many uses in many areas of digital design where complex combinatorial logic comprising multigate trees are employed. The advantages are a saving in electronic P.C. board real estate, cost and offer the ability to reconfigure an electronic system by simply unplugging a ROM and plugging in a new one. The 1702 ROM may then be erased for reuse in about 5 minutes with the model UVS-11 ultra-violet light source manufactured by Ultra Light Products, Inc.

#### Operation

- 1. Turn off power switch.
- 2. Plug in ROM in verify socket (pin 1 key in upper left corner).
- 3. Turn on power.
- 4. Move mode selector toggle to "Verify".
- 5. Advance through all 256 addresses and verify clear memory (all zeros) by using the thumbwheels and address entering push-button.

- 6. Turn off power.
- 7. Transfer ROM to program socket.
- 8. To copy a ROM go to step 18, otherwise go to next step.
- 9. Turn on power.
- 10. Move mode selector toggle to "manual program".
- 11. Set thumbwheels to desired starting address.
- 12. Push "enter address" and verify that correct address has been entered into the display. (Thumbwheels are notorious mechanical beasts and hence sometimes a little shaking is necessary to get the correct address entered.)
- 13. Set up the data with the "data entry" switches according to your truth table.
- 14. Push the "program sequence" push-button. (Verify that faint flickering of the selected address and data bits V , Prog, and V  $_{\rm DD}$  occurs.  $V_{\rm DD}$  is rather bright.)
- 15. After about 5 seconds the machine will stop with the next address displayed.
- 16. When 256 is reached, turn off power and go to step 27.
- 17. Repeat back to step 13 if the next memory address is to be programmed. If not, repeat back to step 11.
- 18. Move mode selector toggle to "copy program".
- 19. Insert master ROM in verify socket.
- 20. Turn on power.
- 21. Set thumbwheels to 000.
- 22. Push "program sequence" push-button.
- 23. Do step 14 and then step 24.
- 24. In about 20 minutes the machine will stop with 256 displayed in the address display.

25. Turn off power.

26. Remove master ROM from verify socket.

- 27. Transfer programmed ROM to verify socket.
- 28. Move mode switch to "verify".
- 29. Turn on power.
- 30. Advance through all 256 addresses and verify data according to your truth table.
- 31. End.

#### Circuit Description

The ROM programmer comprises address sequence control, program data handling, high voltage program power supply control, and various displays and switches to interface with humans. Circuit card 1 contains a 3-decade address counter-latch (chips K, L, and M) with inputs connected to the thumbwheels (see schematic).



The "enter address" push-button grounds pin F-9 when pushed which "latches in" the thumbwheel preset address to the counters. The counter outputs drive the displays (card output pins P-Z) and "BCD" to binary code converter chips A, B, C, D, E, and J. The code converter provides binary sequence outputs to inverters F and H and "verify" ROM address inputs. The inverters drive the address (verify) LED's and are also connected to card C-2 high voltage driver inputs (chips H and J). See schematic for card C-2. The driver outputs are connected to the "programmed" ROM address inputs. This ROM "sits up" at +50 volts so that the driver outputs provide negative pulses to the ROM. The 10 ms pulses occur in



groups of ten with a 2% duty factor so that 5 seconds of time is required for each address. This sequence is controlled by the rest of the logic on card C-2. The oscillator (chip D) sets the speed. Decade dividers (chips C and B) provide timing to gate K-12 which provides a 2% duty factor waveform (time) which enables ultimately the address and data high voltage drivers. Gate K-8 delays the trailing edge of time whereas gate E-10 delays the leading edge of time. These gates operate in such a way that the program pulse occurs fully inside the time span between set-up and release time of all other logic and signals applied to the programmed ROM. This precludes the possibility of spikes occurring internal to the ROM due to race conditions yielding erroneous results. Flip-flops (F) maintain the run status of the machine. Divider (chip A) counts the sequence of ten program pulses and stops and/or advances the address accordingly. The outputs of this counter also drive the serializer comprising chips H and C on card C-3 which provide serial data to a chart recorder for recording. See card schematic C-3. Data entry switch data and "verify" ROM data are both connected to chips M and N which provide program data to the high voltage drivers (chips A and B) providing appropriate negative voltage pulses to the programmed ROM. Chips K and L drive the verify data LED's for display purposes. The "program" address and data display LED's are series connected with the appropriate programmed ROM terminals which provides a monitor of current flow from the ROM. If the ROM is shorted the corresponding LED will light brightly; if open, it will not light at all. Normally during program sequence the LED's flicker dimly according to logic status of the high voltage signals driving the "programmed" ROM. Diodes 1N914 and 470 ohm resistors provide a clamping to -45 V action to the high voltage drivers, thus limiting the negative amplitude according to Intel specification. The error gate J-8 checks the status of the data entry switches and provides a logical zero signal to gate L-11 on card C-2 when all data toggles are set to 1. This is a necessary condition to operate the programmer in the "copy" mode. When the

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mode toggle is placed in the "copy ROM' position, gate L-11 is enabled which drives the error indicator accordingly.

The following schematic presents the various interface, display, and power supply circuits.





FOR	3 OIGIT GENERAL PURPOSE OISPLAY -
	NOEPENOENT / PARALLEL BCO DATA
14 PIN	AUGAT / SCOTCH CABLE FAN OUT -
-	FOR ADDRESS DISPLAY



The next three pages provide specifications for the Intel series ROM's. Some specifications vary in the data (i.e., program time of 2 minutes instead of 20) since some older, low serial number ROM's required more relaxed variables. The programmer should remain timed to provide 20 minute programming time to accommodate the older ROM's. The last pages provide pictures and wire lists of the equipment.





Silicon Gate MOS 1602A/1702A

# 2048 BIT ELECTRICALLY PROGRAMMABLE READ ONLY MEMORY

### 1602A – ELECTRICALLY PROGRAMMABLE 1702A – ERASABLE & ELECTRICALLY REPROGRAMMABLE

- Fast Programming -- 2 minutes for all 2048 bits
- Inputs and Outputs DTL and TTL compatible

Three-state Output --

- All 2048 bits guaranteed\* programmable -- 100% factory tested
- Fully Decoded, 256x8 organization
   Static MOS -- No Clocks Required
- OR-tie Capability

  Simple Memory Expansion --Chip select input lead

The 1602A and 1702A are 256 word by 8 bit electrically programmable ROMs ideally suited for uses where fast turn-around and pattern experimentation are important. The 1602A and 1702A undergo complete programming and functional testing on each bit position prior to shipment, thus insuring 100% programmability.

The 1602A and 1702A use identical chips. The 1702A is packaged in a 24 pin dual in-line package with a transparent quartz lid. The transparent quartz lid allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written into the device. This procedure can be repeated as many times as required. The 1602A is packaged in a 24 pin dual in-line package with a metal lid and is not erasable.

The circuitry of the 1602A/1702A is entirely static; no clocks are required.

A pin-for-pin metal mask programmed ROM, the Intel 1302, is ideal for large volume production runs of systems initially using the 1602A or 1702A.

The 1602A/1702A is fabricated with silicon gate technology. This low threshold technology allows the design and production of higher performance MOS circuits and provides a higher functional density on a monolithic chip than conventional MOS technologies.



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ROMs

### Silicon Gate MOS 1602A/1702A

#### PIN CONNECTIONS

The external lead connections to the 1602A/1702A differ, depending on whether the device is being programmed<sup>(1)</sup> or used in read mode. (See following table)

PIN	12 (V <sub>CC</sub> )	13 (Program)	14 (CS)	15 (V <sub>BB</sub> )	16 (V <sub>GG</sub> )	22 (V <sub>cc</sub> )	23 (V <sub>CC</sub> )
Read	V <sub>cc</sub>	Vcc	GND	Vcc	V <sub>GG</sub>	Vcc	Vcc
Programming	GND	Program Pulse	GND	VBB	Pulsed VGG (VILAP)	GND	GND

#### **Absolute Maximum Ratings\***

Ambient Temperature Under Bias 0°C to +70°C
Storage Temperature
Soldering Temperature of Leads (10 sec)
Power Dissipation
lead Operation: Input Voltages and Supply
Voltages with respect to V <sub>CC</sub> +0.5V to -20V
Program Operation: Input Voltages and Supply
Voltages with respect to V <sub>CC</sub>

#### \*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

### **READ OPERATION**

#### **D.C. and Operating Characteristics**

 $T_A = 0^{\circ}C$  to 70°C,  $V_{CC} = +5V\pm5\%$ ,  $V_{DD} = -9V\pm5\%$ ,  $V_{GC}^{(2)} = -9V\pm5\%$ , unless otherwise noted

SYMBOL	TEST	MIN.	TYP!	3) MAX.	UNIT	CONDITIONS	
1 <sub>L1</sub>	Address and Chip Select Input Load Current			1	μA	V <sub>IN</sub> = 0.0V	
LO	Output Leakage Current			1	μA	$V_{OUT} = 0.0V, \overline{CS} = V_{CC} - 2$	
IDDO	Power Supply Current		5	10	mA	$V_{GG} = V_{CC}, \overline{CS} = V_{CC} - 2$ $I_{OL} = 0.0 \text{mA}, T_A = 25^{\circ}\text{C}$	
I <sub>DD1</sub>	Power Supply Current		35	50	mA	CS=V <sub>CC</sub> -2 I <sub>OL</sub> =0.0mA, T <sub>A</sub> = 25°C	)
I <sub>DD2</sub>	Power Supply Current		32	46	mA	CS=0.0 I <sub>OL</sub> =0.0mA, T <sub>A</sub> = 25°C	
I <sub>DD3</sub>	Power Supply Current		38.5	60	mA	CS=V <sub>CC</sub> −2 I <sub>OL</sub> =0.0mA , T <sub>A</sub> = 0°C	Operation
I <sub>CF1</sub>	Output Clamp Current		8	14	mA	$V_{OUT} = -1.0V, T_A = 0^{\circ}C$	
ICF2	Output Clamp Current			13	mA	$V_{OUT} = -1.0V, T_A = 25^{\circ}C$	ļ
I <sub>GG</sub>	Gate Supply Current			1	μA		
VIL1	Input Low Voltage for TTL Interface	-1.0		0.65	v		
Vil2	Input Low Voltage for MOS Interface	VDD		V <sub>CC</sub> –6	v		
V <sub>IH</sub>	Address and Chip Select Input High Voltage	V <sub>cc</sub> -2		V <sub>CC</sub> +0.3	v		
IOL I	Output Sink Current	1.6	4		mA	V <sub>OUT</sub> = 0.45V	
юн	Output Source Current	-2.0			mA	V <sub>OUT</sub> = 0.0V	
VOL	Output Low Voltage		7	0.45	v	I <sub>OL</sub> = 1.6mA	A Contraction of the
VOH	Output High Voltage	3.5	4.5		v	lou = -100 #A	

Note 2: VgG may be clocked to reduce power dissipation in this mode average IDD increases in proportion to VGG duty cycle. (See p. 5) Note 3: Typical values are at nominal voltages and T<sub>A</sub> =  $25^{\circ}$ C

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## Silicon Gate MOS 1602A/1702A

ROMs

#### A.C. Characteristics

 $T_{A} = 0^{\circ}$ C to +70°C,  $V_{CC} = +5V \pm 5\%$ ,  $V_{DD} = -9V \pm 5\%$ ,  $V_{GG} = -9V \pm 5\%$  unless otherwise noted

SYMBOL	TEST	MINIMUM	TYPICAL	MAXIMUM	UNIT
Freq.	Repetition Rate		f	1	MHz
t <sub>OH</sub>	Previous reed data valid			100	ns
TACC	Address to output delay		.700	1	μs
tovgg	Clocked V <sub>GG</sub> set up	0			μs
tcs	Chip select delay			100	ns
t <sub>00</sub>	Output delay from CS			900	ns
top	Output deselect			300	ns
t <sub>DHC</sub>	Data out hold in clocked VGG mode (Note 1)			5	μs

Note 1. The autput will remain valid for t<sub>OHC</sub> as long as clocked V<sub>GG</sub> is at V<sub>CC</sub>. An address change may occur as soon as the autput is sensed (clocked V<sub>GG</sub> may still be at V<sub>CC</sub>). Data becomes invalid for the old address when clocked V<sub>GG</sub> is returned to V<sub>GG</sub>.

### Capacitance\* T\_ = 25°C

SYMBOL	TEST	MINIMUM	TYPICAL	MAXIMUM	UNIT	CONDITIONS
Cin	input Capacitance		8	15	pF	
COUT	Output Capacitance		10	15	pF	CS = V <sub>CC</sub> unused pins
CVGG	V <sub>GG</sub> Capacitance (Clocked V <sub>GG</sub> Mode)			30	pF	$V_{GG} = V_{CC}$ ground

"This parameter is periodically sampled and is not 100% tested.

#### Switching Characteristics







### Silicon Gate MOS 1602A/1702A

#### **Typical Characteristics**







OUTPUT SINK CURRENT



AVERAGE CURRENT VS. DUTY CYCLE FOR CLOCKED VGG





TTL LOAD

Voc - +8V

Vnn -- 8V

inn

20 20 00 00 70

LOAD CAPACITANCE (AF)





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#### ROMs

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### Silicon Gate MOS 1602A/1702A

ROMs

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## **PROGRAMMING OPERATION**

### D.C. and Operating Characteristics for Programming Operation

 $T_{A}$  = 25°C,  $V_{CC}$  = 0V,  $V_{BB}$  = +12V  $\pm$  10%,  $\overline{CS}$  = 0V unless otherwise noted

SYMBOL	TEST	MIN.	TYP.	MAX.	UNIT	CONDITIONS
ILIIP	Address and Data Input Load Current			10	mA	V <sub>IN</sub> = -48V
IL 12P	Program and V <sub>GG</sub> Load Current			10	mA	V <sub>IN</sub> = -48V
I <sub>B B</sub>	V <sub>BB</sub> Supply Load Current		.05		mA	
IDDP <sup>(1)</sup>	Peak I <sub>DD</sub> Supply Load Current		200		mA	$V_{DD} = V_{prog} = -48V$ $V_{GG} = -35V$
VIHP	Input High Voltage			0.3	V	
VILIP	Pulsed Data Input Low Voltage	-46		-48	v	
V <sub>IL2P</sub>	Address Input Low Voltage	-40		-48	v	
VIL3P	Pulsed Input Low V <sub>DD</sub> and Program Voltage	-46		-48	v	
V <sub>IL4P</sub>	Pulsed Input Low V <sub>GG</sub> Voltage	-35		-40	V	

Note 1: IDDP flows only during VDD, VGG on time. IDDP should not be allowed to exceed 300 mA for greater then 100µsec. Average power supply current IDDP is typically 40mA at 20% duty cycle.

#### A.C. Characteristics for Programming Operation

 $T_{AMBIENT} = 25^{\circ}C, V_{CC} = 0V, V_{BB} = + 12V \pm 10\%, \overline{CS} = 0V$  unless otherwise noted

SYMBOL	TEST	MIN.	TYP.	MAX.	UNIT	CONDITIONS
	Duty Cycle (V <sub>DD</sub> , V <sub>GG</sub> )			20	%	
t <sub>øPW</sub>	Program Pulse Width			3	ms	V <sub>GG</sub> = -35V, V <sub>DD</sub> = V <sub>prog</sub> = -48V
tow	Data Set Up Time	25			μs	
tDH	Data Hold Time	10			μs	
tvw	V <sub>DD</sub> , V <sub>GG</sub> Set Up	100			μs	
t <sub>VD</sub>	V <sub>DD</sub> , V <sub>GG</sub> Hold	10		100	μs	
tACW (2)	Address Complement Set Up	25			μs	
tACH (2)	Address Complement Hold	25			μs	
tATW	Address True Set Up	10			μs	
tATH	Address True Hold	10			μs	

Note 2. All 8 address bits must be in the complement state when pulsed V<sub>DD</sub> and V<sub>GG</sub> move to their negative levels. The addresses (0 through 255) must be programmed as shown in the timing diagram for a minimum of 32 times.

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### Silicon Gate MOS 1602A/1702A

### Switching Characteristics for Programming Operation

PROGRAM OPERATION

Conditions of Test:

Input pulse rise and fall times  $\leq 1\mu$ sec  $\overline{CS} = 0V$ 

PROGRAM WAVEFORMS



#### Programming Operation of the 1602A/1702A

When the Data Input for the Program Mode is:	Then the Data Output during the Read Mode is:	WORD
VILIP = ~48V pulsed	Logic 1 = V <sub>OH</sub> = 'P' on tape	0
V <sub>IHP</sub> = ~ 0V	Logic 0 = V <sub>OL</sub> ='N' on tape	255

	ADDRESS											
WORD	A7	A6	A5	A4	A3	A2	<b>A</b> 1	Ao				
0	0	0	0	0	0	0	0	0				
1	1 0	0	0	0	0	0	0	+				
1	1 1	1	1	1	1	1	1	1				
i	1	1	1	i.	1	1	1	1				
255	1	1	1	1	1	1	1	1				
3V) Logic	1 = VIII (~3V											

Address Logic Level During Read Mode: Logic 0 =  $V_{1L}$  (~.3V) Logic 1 =  $V_{1H}$  (~3V) Address Logic Level During Program Mode: Logic 0 =  $V_{1L2P}$  (~-40V) Logic 1 =  $V_{1HP}$  (~0V) ROMs

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A ROM VERIFY

B ROM PROGRAM



	CARD SLOT WIRING LIST				CARD SLOT WIRING LIST				CARD SLOT WIRING LIST				
FOR:	BOX <u>Rom</u>	Programmer/Verifier	CARD	<u> </u>	FOR: BOX ROM P	rogrammer/Verifier CA	RD	C-2	FOR: BOX	ROM Pr	ogrammer/Verifier_	CARD	C-3
	Fron	<u> </u>	From	To	From	<u>To</u>	From	To		From	To	From	To
Slot _	<u>1</u> A	Gnd	1	GNd	Slot A	Gnd	1	Gnd	Slot	· A	Gnd	_ 1	Gnd
1	Y Buss B	+5	2	+5	В	+5	2	+5		в	+5	_ 2	+5
	X Buss C	<u>1 - TW</u>	. 3	S2-C	С		3			С	SO-B	_ 3	
(	D	<u>2 - TW</u>	. 4	<u>S2-D</u>	D		4			D		_ 4	
Address	E	4 - TW	5	S2-E	E		5			Е	SO-D	_ 5	
Select Thumb-	F	8 - TW	6	S2-F	F		8			F	SO-E	_ 6	<u></u>
wheels	н	10 - TW	. 7	S2-H	н		7			н	SO-F	_ 7	
	J	<u>20 - TW</u>	. 8	S2-J	J		8			J	SO-H	8	
	к	40 - TW	9	S2-K	к		9			к	SOJ	_ 9	
]	L	80 - TW	10	S2-L	L		10			L	SO-K	10	
l	м	<u> 100 - TW</u>	. 11	<u>\$0-2</u>	м		11	S3-M		М		_ 11	+50 V DC
	N	200 - TW	12	SO-3	N		12			N		12	
	P		13	SO-4	Р		13	<u>\$3-X</u>		P		13	
	R		14	SO-5	R	NC	14	NC		R		14	
	8		15	SO-6	s		15	<u>so-20</u>		s	. <u></u>	15	
	Ť		16	<u>so_7</u>	т	NC	18	SO-X		T		18	
	U		. 17	SO-8	U	+50 V DC	17	<u>NC</u>		U		17	
	v		18	SO-9	v	<u>NC</u>	18			v		18	
	w		19	\$2-W	w		19	NC		w		19	
	x		20	S2-X	x		20	NC		х		20	
	Y		21	<u> </u>	Y	S3-21	21	S3-Y		Y		21	
	z		. 22	<u>S2-Z</u>	z	<u></u>	22	\$3-Z		Z		22	
Abbre	viations:	BNC Cont	nectors: B1,	B2, B3, etc.	Abbreviations:	BNC Connectors	s: B1,	B2, B3, etc.	Abbreviations:		BNC Con	nectors: Bl	., B2, B3, etc.
Ex: S	25-22	Elco Conr	nectors: J1.	J2, J3. etc.	Ex: S 25-22	Elco Connector	s: J1,	J2, J3, etc.	Ex: S 25-22		Elco Con	nectors: J1	, J2, J3, etc.
8	10t 25, Pin 22	Slot Con	nectors: S1,	S2, S3, etc.	Slot 25, Pin 22	Slot Connector:	s: S1,	S2, S3, etc.	Slot 25, P	11 22	Slot Con	nectors: S1	, S2, S3, etc.
J F	9-MM lco J9, Pin MM	Pin No.'s	• <del>-</del> 3.	-X, -B, -22, etc.	J9-MM Elco J9, Pin MM	Pin No.'s	<b>-3</b> ,	-X, -B, -22, etc.	<b>J9-MM</b> Elco <b>J9</b> , 1	Pin MM	Pin No.'	s -3	X, -B, -22, etc.

USE BUSS WIRE WHENEVER POSSIBLE TO NAME CONNECTIONS TO ADJACENT CARDS.



